

**RESURF LDMOS INTEGRATED STRUCTURE**

**Abstract of the Disclosure**

A reduced surface field (RESURF) lateral  
diffused metal oxide semiconductor (LDMOS) integrated  
circuit includes a first region having a first  
5 conductivity type defined in a semiconductor substrate  
having a second conductivity type, a body region having  
the second conductivity type in the first region, and a  
source region having the first conductivity type formed  
in the body region. More specifically, the body region  
10 may be within a surface portion of the first region  
that is more heavily doped than the remainder of the of  
the first region.